

ABSTRACT OF THE DISCLOSURE

There is provided a semiconductor device having a ferroelectric capacitor, which comprises capacitor protection films for covering an upper surface and a side surface the ferroelectric capacitor that is formed on a first insulating film, a hole formed in a second insulating film, which is formed on the capacitor protection films and the first insulating film, to be positioned adjacently to the side surface of the ferroelectric capacitor via the capacitor protection films, and a conductive plug formed in the hole. Accordingly, alignment margin of the contact hole to be formed next to the capacitor can be reduced.